



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92MOD Plastic-Encapsulate Transistors

2SC2229 TRANSISTOR (NPN)

FEATURE

Power dissipation

P_{CM} : 0.8 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 0.05 A

Collector-base voltage

$V_{(BR)CBO}$: 200 V

Operating and storage junction temperature range

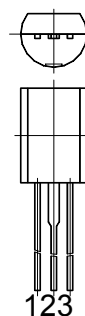
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

TO-92MOD

1. EMITTER

2. COLLECTOR

3. BASE



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100\mu A, I_E = 0$	200		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1mA, I_B = 0$	150		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100\mu A, I_C = 0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB} = 200V, I_E = 0$		0.1	μA
Collector cut-off current	I_{CER}	$V_{CB} = 150V, R_{EB} = 10M\Omega$		1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V, I_C = 0$		0.1	μA
DC current gain	h_{FE}	$V_{CE} = 5V, I_C = 10mA$	70	240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10mA, I_B = 1mA$		0.5	V
Base-emitter voltage	$V_{BE(sat)}$	$I_C = 10mA, I_B = 1mA$		1	V
Transition frequency	f_T	$V_{CE} = 30V, I_C = 10mA$ $f = 30MHz$	80		MHz

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	70-140	120-240

